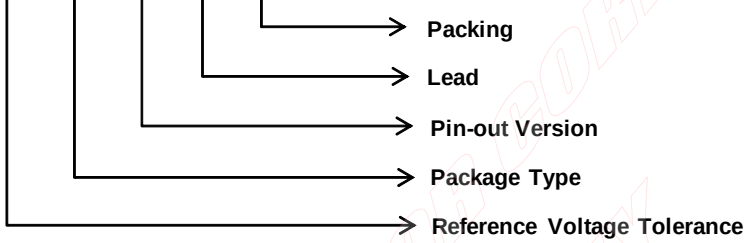
Ordering Information

LT 431 X X X X X



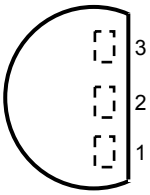
Reference Voltage Tolerance	Package Type	Pin-out Version	Lead	Packing
O : ±0.4% N : ±1.0%	H : TO92-3L C : SOT23-3L	Blank (TO92-3L): 1. REF 2. ANODE 3. CATHODE A (SOT23-3L): 1. CATHODE 2. REF 3. ANODE R (SOT23-3L): 1. REF 2. CATHODE 3. ANODE	P : RoHS & Halogen Free (ref. IEC 61249-2-21)	A : Tape & Reel

Product Number	Output Voltage Tolerance	Package	Lead	Packing
LT431OHPA	0.4 %	TO92-3L	RoHS& Halogen Free	Taping
LT431NHPA	1.0 %	TO92-3L	RoHS& Halogen Free	Taping
LT431OCAPA	0.4 %	SOT23-3L	RoHS& Halogen Free	Taping & Reel
LT431NCAPA	1.0 %	SOT23-3L	RoHS& Halogen Free	Taping & Reel
LT431OCRPA	0.4 %	SOT23-3L	RoHS& Halogen Free	Taping & Reel
LT431NCRPA	1.0 %	SOT23-3L	RoHS& Halogen Free	Taping & Reel

Pin Assignment

TO92-3L

(Top View)

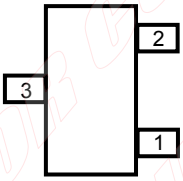


LT431OHPA
LT431NHPA

1.R
2.A
3.C

SOT23-3L

(Top View)

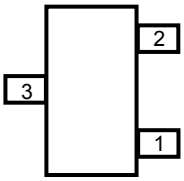


LT431OCAPA
LT431NCAPA

1.C
2.R
3.A

SOT23-3L

(Top View)



LT431OCRPA
LT431NCRPA

1.R
2.C
3.A

Pin Descriptions

Pin Name	Pin Description
R	Ref
A	Anode
C	Cathode

Absolute Maximum Ratings(at T_A=25°C)

Note: Operate over the “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to such conditions for extended time may still affect the reliability of the device.

Characteristics		Symbol	Rating	Unit
Cathode Voltage		V_{KA}	40	V
Continuous Cathode Current		I_{KA}	250	mA
Reference Input Current		I_{REF}	10	mA
Junction Temperature		T_J	160	°C
Storage Temperature		T_{STG}	-40~150	°C
Thermal Resistance (Junction to Case)	SOT23-3L	θjc	110	°C/W
	TO92-3L		80	
Thermal Resistance (Junction to Ambient)	SOT23-3L	θja	350	°C/W
	TO92-3L		150	
Power dissipation	SOT23-3L	P_D	285	mW
	TO92-3L		625	
Moisture Sensitivity		MSL	Please refer the MSL label on the IC package bag/carton for detail	

Note1 : Ratings apply to ambient temperature at 25°C

Recommended Operating Conditions

Characteristics	Symbol	Min	Max	Unit
Cathode Voltage	V_{KA}	V_{REF}	36	V
Cathode Current	I_{KA}	0.5	200	mA
Operating Temperature (Operating free-air temperature)	T_A	-20	85	°C

Electrical Characteristics

(T_A=25°C, unless otherwise specified)

Characteristics	Symbol	Conditions		Min	Typ	Max	Unit
Reference Voltage	V_{REF}	V_{KA} = V_{REF}, I_{KA} = 10mA (Fig.1)	0.4 %	2.485	2.495	2.505	V
			1.0 %	2.470		2.520	
Deviation of Reference Input Voltage over full temperature Range(*Note 2)	$V_{REF(DEV)}$	V_{KA} = V_{REF}, I_{KA} = 10mA, T_A = -20~85°C (Fig.1)			6.0	20	mV
Reference Input Current	I_{REF}	R1 = 10KΩ,R2 = ∞ I_{KA}= 10mA (Fig.2)			1.5	3.5	uA
Deviation of Reference Input Current over Temperature	$I_{REF(DEV)}$	R1 = 10KΩ,R2 = ∞ I_{KA} = 10mA T_A = -20~85°C (Fig.2)			0.4	1.2	uA
Ratio of the Change in Reference V_{KA} = 10V ~V_{REF} - -1.2 -2.0 Voltage to the Change in Cathode Voltage	$\frac{\Delta V_{REF}}{\Delta V_{KA}}$	I_{KA} = 10mA (Fig.2)	V_{KA} = 10V ~V_{REF}		-1.2	-2.0	mV/V
			V_{KA}= 36V ~10V		-1	-2.0	
Minimum Cathode Current for Regulation	$I_{KA(min)}$	V_{KA} = V_{REF} (Fig.1)			0.2	0.5	mA
Off-state Cathode Current	$I_{KA(OFF)}$	V_{KA} = 36V, V_{REF} = 0V (Fig.3)			0.1	1	uA
Dynamic Output Impedance	Z_{KA}	V_{KA} = V_{REF} Frequency ≤ 1KHz (Fig.1)			0.2	0.5	Ω

Note 2 : Thes speicifications are guaranteed by designed and are not tested when in mass-production.

Application Circuit

Fig1: $V_{KA}=V_{REF}$

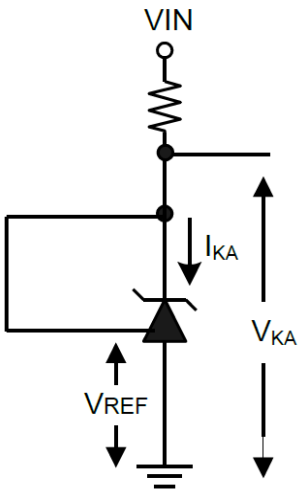
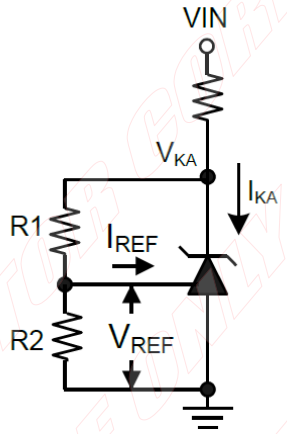
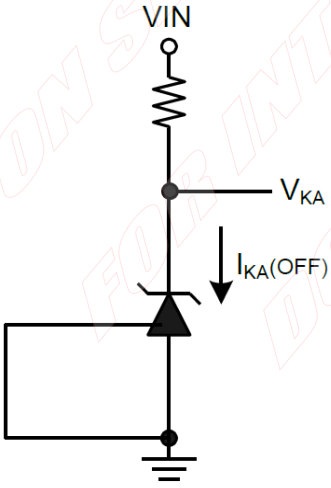


Fig2: $V_{KA}>V_{REF}$

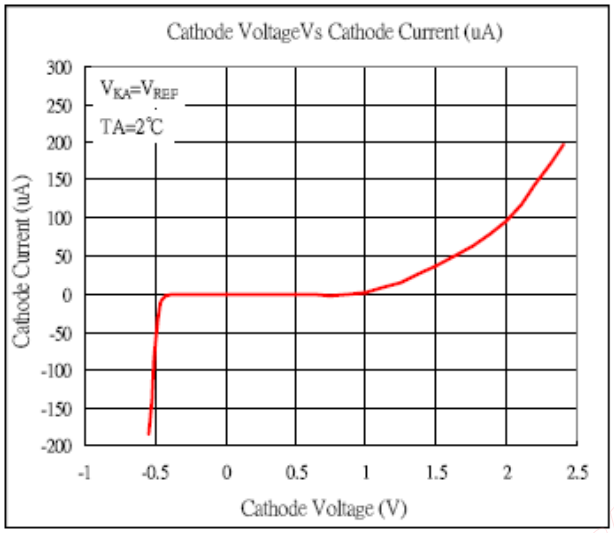


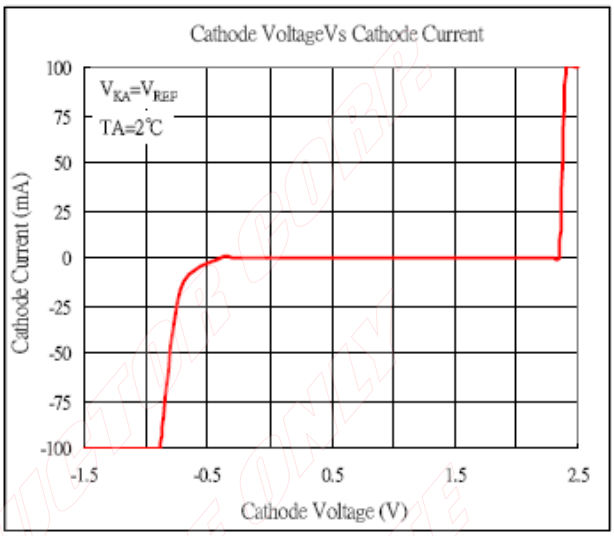
$VKA=V_{REF}(1+R1/R2)+I_{REF}*R1$

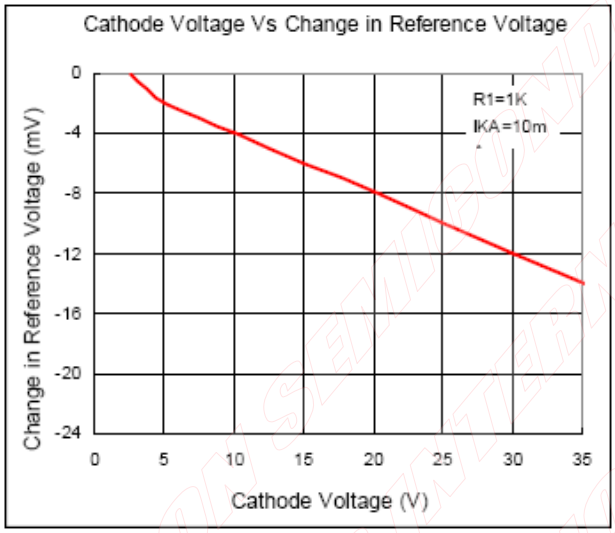
Fig3: Off state current

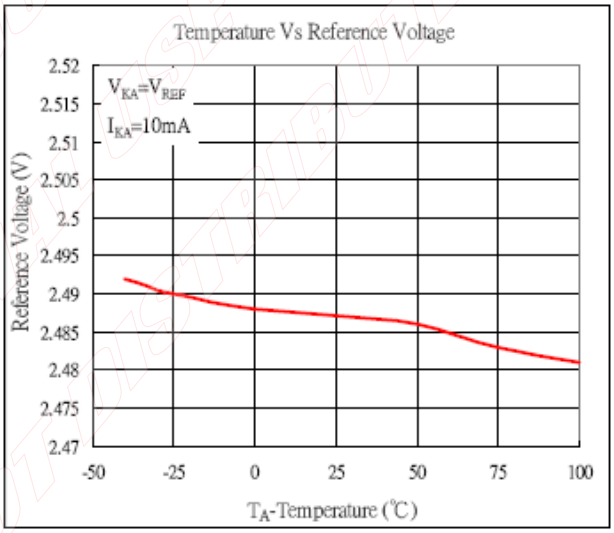


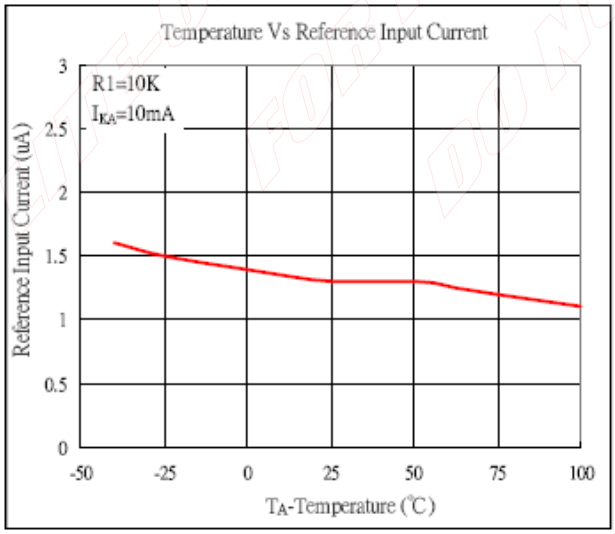
Typical Characteristics





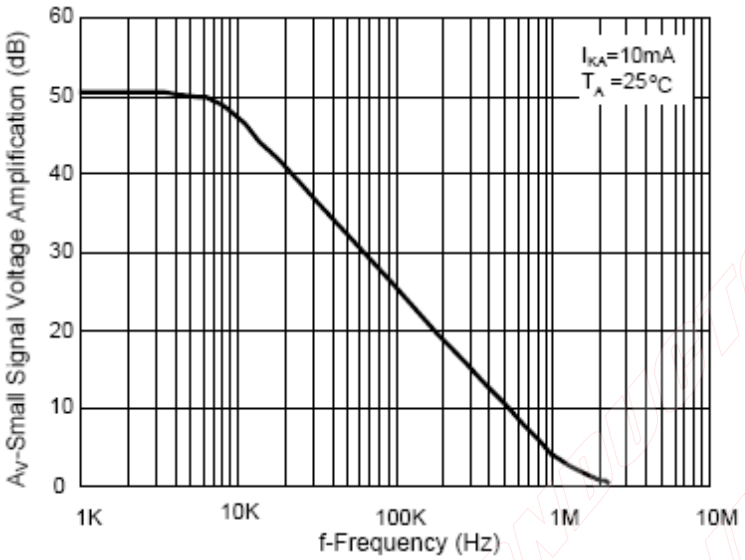


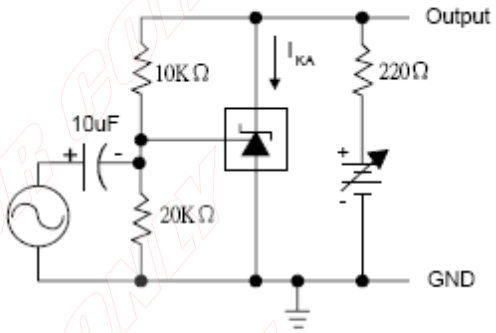




Typical Characteristics(Continued)

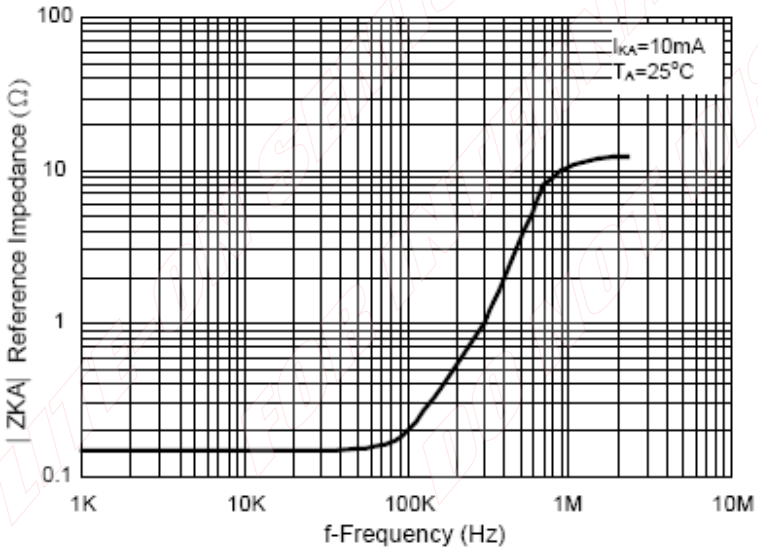
(1) Small Signal Voltage Amplification Vs Frequency

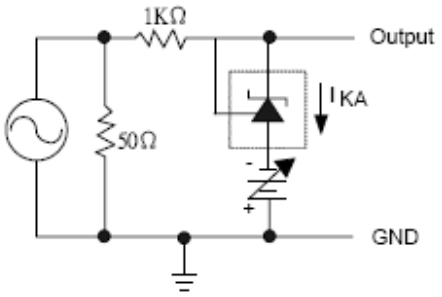




TEST CIRCUIT FOR VOLTAGE AMPLIFICATION

(2) Reference Impedance VS Frequency

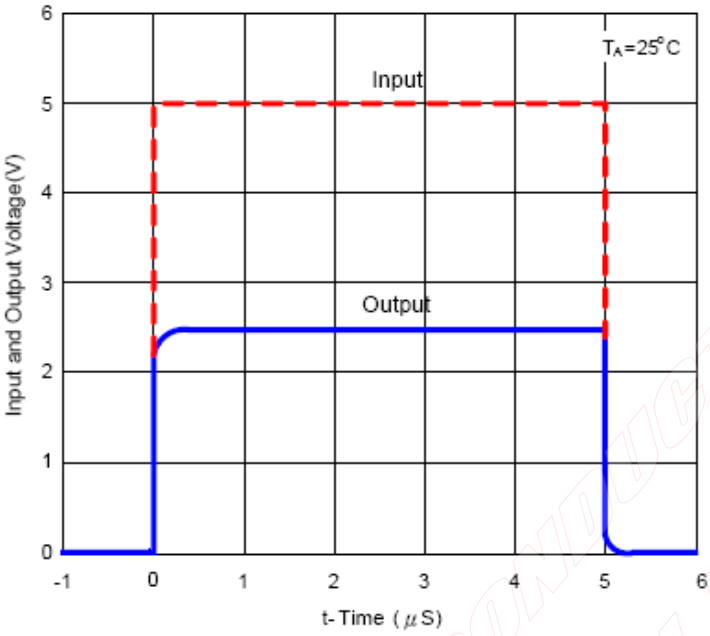


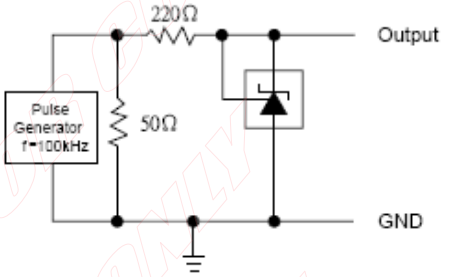


TEST CIRCUIT FOR REFERENCE IMPEDANCE

Typical Characteristics (Continued)

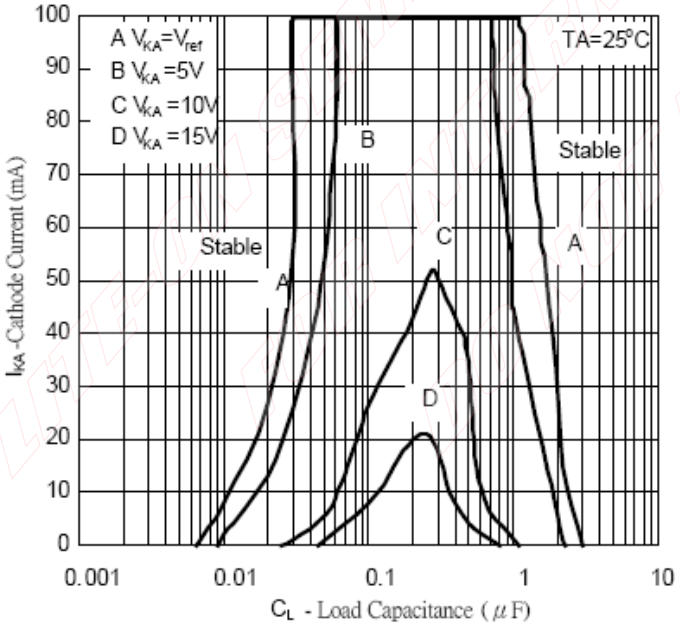
(3) Pulse Response

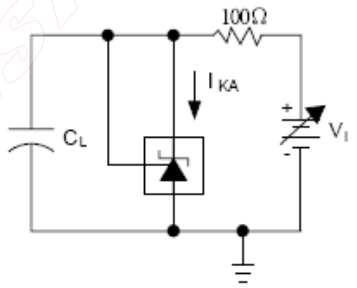




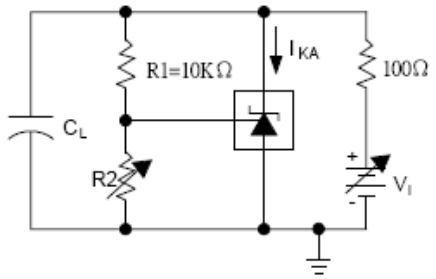
TEST CIRCUIT FOR PULSE RESPONSE

(4) Stability boundary conditions





TEST CIRCUIT FOR CURVE A

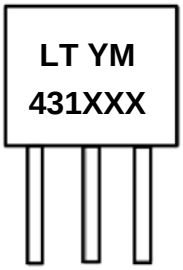


TEST CIRCUIT FOR CURVE B , C , AND D

The areas under the curves represent conditions that may cause the device to oscillate For curves B,C , and D, R2 and V_I were adjusted to establish the initial V_{KA} and I_{KA} conditions with C_L=0 . V_{BATT} and C_L were then adjusted to determine the ranges of stability.

Marking Information

(1) TO92-3L



1) YM = Date Code,

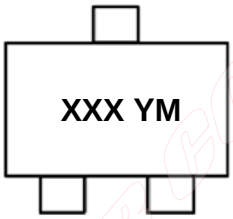
Y: Year, M: Month

2) 431xxx = Marking Code

LT431OHPA: 431OHP

LT431NHPA: 431NHP

(2) SOT23-3L



1) YM = Date Code,

Y: Year, M: Month

2) xxx = Marking Code

LT431OCAPA: OCA

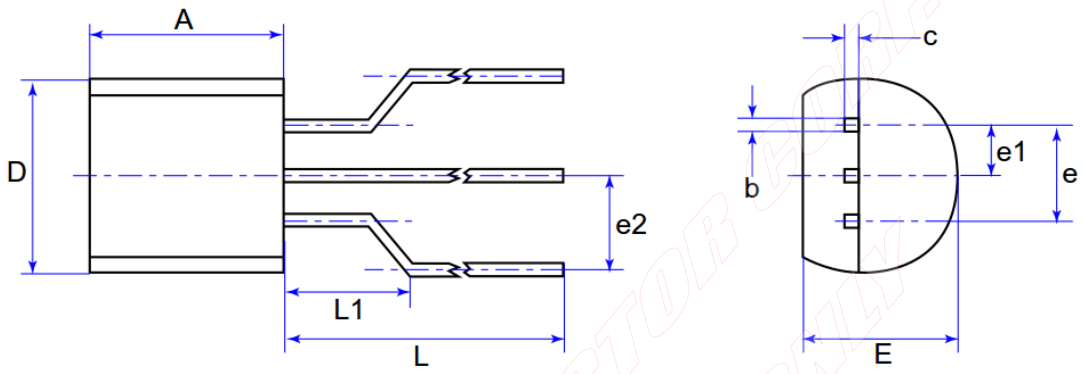
LT431NCAPA: NCA

LT431OCRPA: OCR

LT431NCRPA: NCR

Mechanical Information

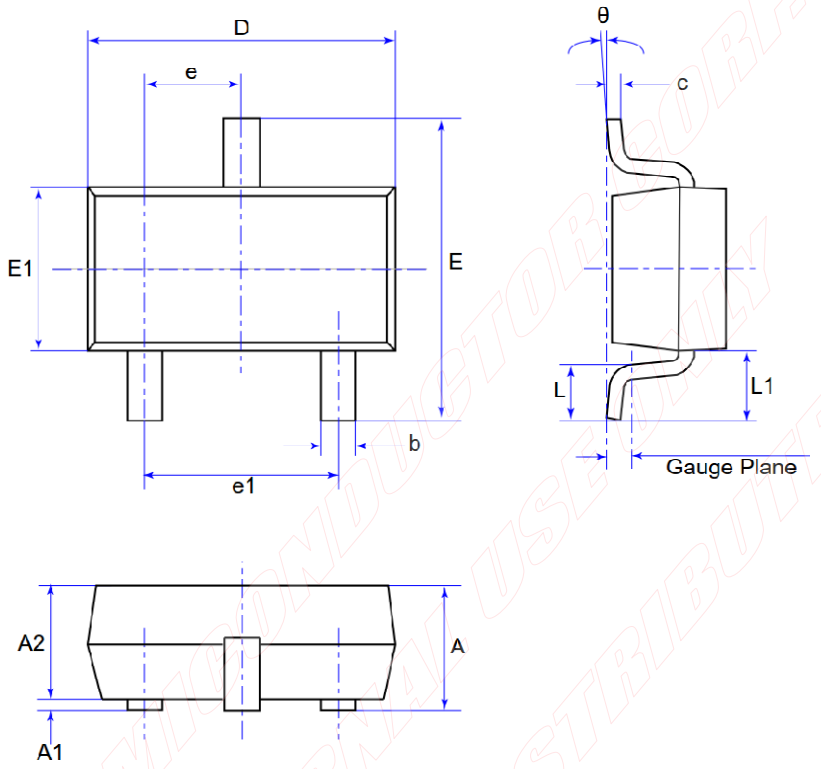
(1) Package type: TO92-3L



Symbol	Min	Max
A	4.30	4.70
b	0.38	0.55
c	0.36	0.51
D	4.30	4.70
E	3.30	3.70
e	2.44	2.64
e1	1.27 TYP	
e2	2.20	2.80
L	13.00	14.00
L1	2.50	4.50

Mechanical Information (Continued)

(2) Package type: SOT23-3L



Unit: mm

Symbol	Min	Max
A	0.90	1.15
A1	-	0.10
A2	0.89	1.05
b	0.30	0.50
c	0.07	0.18
D	2.80	3.04
E	2.10	2.64
E1	1.20	1.40
e	0.95 REF	
e1	1.80	2.00
L	0.30	0.50
L1	0.55 REF	
Gauge Plane	0.25 BSC	
θ	0°	8°

MSL (Moisture Sensitive Level) Information

IPC/JEDEC J-STD-020D.1 Moisture Sensitivity Levels Table

LEVEL	FLOOR LIFE		SOAK REQUIREMENTS				
			Standard		Accelerated Equivalent [1]		
					eV 0.40-0.48	eV 0.30-0.39	CONDITION
	TIME	CONDITION	TIME (hours)	CONDITION	TIME (hours)	TIME (hours)	
1	Unlimited	≤30 °C /85% RH	168 +5/-0	85 °C /85% RH	NA	NA	NA
2	1 year	≤30 °C /60% RH	168 +5/-0	85 °C /60% RH	NA	NA	NA
2a	4 weeks	≤30 °C /60% RH	696[2] +5/-0	30 °C /60% RH	120 -1/+0	168 -1/+0	60 °C/ 60% RH
3	168 hours	≤30 °C /60% RH	192[2] +5/-0	30 °C /60% RH	40 -1/+0	52 -1/+0	60 °C/ 60% RH
4	72 hours	≤30 °C /60% RH	96[2] +2/-0	30 °C /60% RH	20 +0.5/-0	24 +0.5/-0	60 °C/ 60% RH
5	48 hours	≤30 °C /60% RH	72[2] +2/-0	30 °C /60% RH	15 +0.5/-0	20 +0.5/-0	60 °C/ 60% RH
a	24 hours	≤30 °C /60% RH	48[2] +2/-0	30 °C /60% RH	10 +0.5/-0	13 +0.5/-0	60 °C/ 60% RH
6	Time on Label (TOL)	≤30 °C /60% RH	TOL	30 °C /60% RH	NA	NA	NA

Note 1: CAUTION - To use the ‘‘accelerated equivalent’’ soak conditions, correlation of damage response (including electrical, after soak and reflow), should be established with the ‘‘standard’’ soak conditions. Alternatively, if the known activation energy for moisture diffusion of the package materials is in the range of 0.40 - 0.48 eV or 0.30 - 0.39 eV, the ‘‘accelerated equivalent’’ may be used. Accelerated soak times may vary due to material properties (e.g .mold compound, encapsulant, etc.). JEDEC document JESD22-A120 provides a method for determining the diffusion coefficient.

Note 2: The standard soak time includes a default value of 24 hours for semiconductor manufacturer’s exposure time (MET) between bake and bag and includes the maximum time allowed out of the bag at the distributor’s facility. If the actual MET is less than 24 hours the soak time may be reduced. For soak conditions of 30 °C/60% RH, the soak time is reduced by 1 hour for each hour the MET is less than 24 hours. For soak conditions of 60 °C/60% RH, the soak time is reduced by 1 hour for each 5 hours the MET is less than 24 hours. If the actual MET is greater than 24 hours the soak time must be increased. If soak conditions are 30 °C/60% RH, the soak time is increased 1 hour for each hour that the actual MET exceeds 24 hours. If soak conditions are 60 °C/60% RH, the soak time is increased 1 hour for each 5 hours that the actual MET exceeds 24 hours.